THE DATASHEET OF

CSD16325Q5C

DualCool™ N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16325Q5C

FEATURES

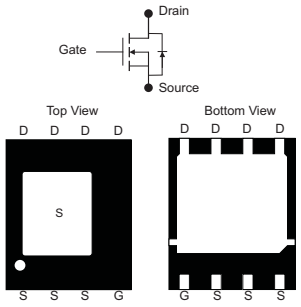
- **DualCool™ Package SON 5×6mm**
- **Optimized for 2-Sided Cooling**
- **Optimized for 5V Gate Drive**
- **Ultralow Q_g and Q_{gd}**
- **Low Thermal Resistance**
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant and Halogen Free**

APPLICATIONS

- **Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems**
- **Optimized for Synchronous FET Applications**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.



PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25		V
Q_g	Gate Charge Total (4.5V)	18		nC
Q_{gd}	Gate Charge Gate to Drain	3.5		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V	2.1	mΩ
		V_{GS} = 4.5V	1.7	mΩ
		V_{GS} = 8V	1.5	mΩ
$V_{GS(th)}$	Threshold Voltage	1.1		V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16325Q5C	SON 5×6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

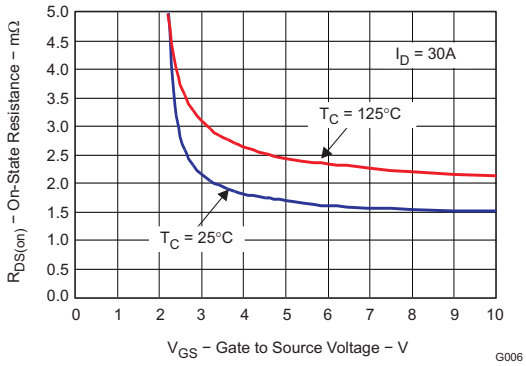
ABSOLUTE MAXIMUM RATINGS

T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / –8	V
I_D	Continuous Drain Current, T_C = 25°C	100	A
	Continuous Drain Current(1)	33	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	200	A
P_D	Power Dissipation(1)	3.1	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse I_D = 100A, L = 0.1mH, R_G = 25Ω	500	mJ

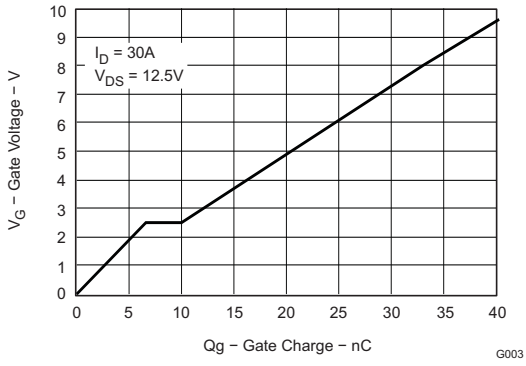
(1) Typical $R_{\theta JA}$ = 38°C/W on 1-in^2 Cu, (2-oz.) on a 0.060" thick FR4 PCB.

(2) Pulse duration ≤300μs, duty cycle ≤2%

$R_{DS(on)}$ vs V_{GS}



Gate Charge



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

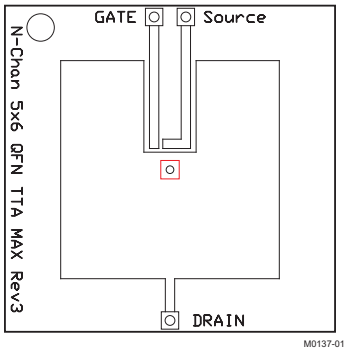
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = 250μA	25			V
I_{DSS}	Drain to Source Leakage	V_{GS} = 0V, V_{DS} = 20V			1	μA
I_{GSS}	Gate to Source Leakage	V_{DS} = 0V, V_{GS} = +10/–8V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	0.9	1.1	1.4	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V, I_D = 30A		2.1	2.9	mΩ
		V_{GS} = 4.5V, I_D = 30A		1.7	2.2	mΩ
		V_{GS} = 8V, I_D = 30A		1.5	2	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_D = 30A		159		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz		3070	4000	pF
C_{oss}	Output Capacitance			2190	2850	pF
C_{rss}	Reverse Transfer Capacitance			120	150	pF
R_G	Series Gate Resistance			1.6	3.2	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 12.5V, I_{DS} = 30A		18	25	nC
Q_{gd}	Gate Charge – Gate to Drain			3.5		nC
Q_{gs}	Gate Charge – Gate to Source			6.6		nC
$Q_{g(th)}$	Gate Charge at Vth			3.1		nC
Q_{oss}	Output Charge	V_{DS} = 13V, V_{GS} = 0V		43		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 12.5V, V_{GS} = 4.5V, I_{DS} = 30A , R_G = 2Ω		10.5		ns
t_r	Rise Time			16		ns
$t_{d(off)}$	Turn Off Delay Time			32		ns
t_f	Fall Time			12		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{DS} = 30A, V_{GS} = 0V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DD} = 13V, I_F = 30A, di/dt = 300A/μs		63		nC
t_{rr}	Reverse Recovery Time			47		ns

THERMAL CHARACTERISTICS

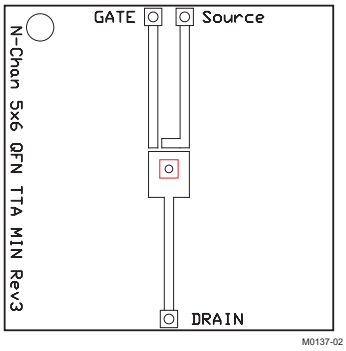
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (Top Source) (1)			1.4	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case (Bottom drain) (1)			1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1) (2)			50	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 2-oz. Cu pad on a 1.5 × 1.5-inch 0.060-inch thick FR4 board. $R_{\theta JC}$ is specified by design, whereas $R_{\theta CA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 of 2-oz. Cu.



Max $R_{\theta JA}$ = 50°C/W when mounted on 1 inch^2 of 2-oz. Cu.



Max $R_{\theta JA}$ = 126°C/W when mounted on minimum pad area of 2-oz.Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

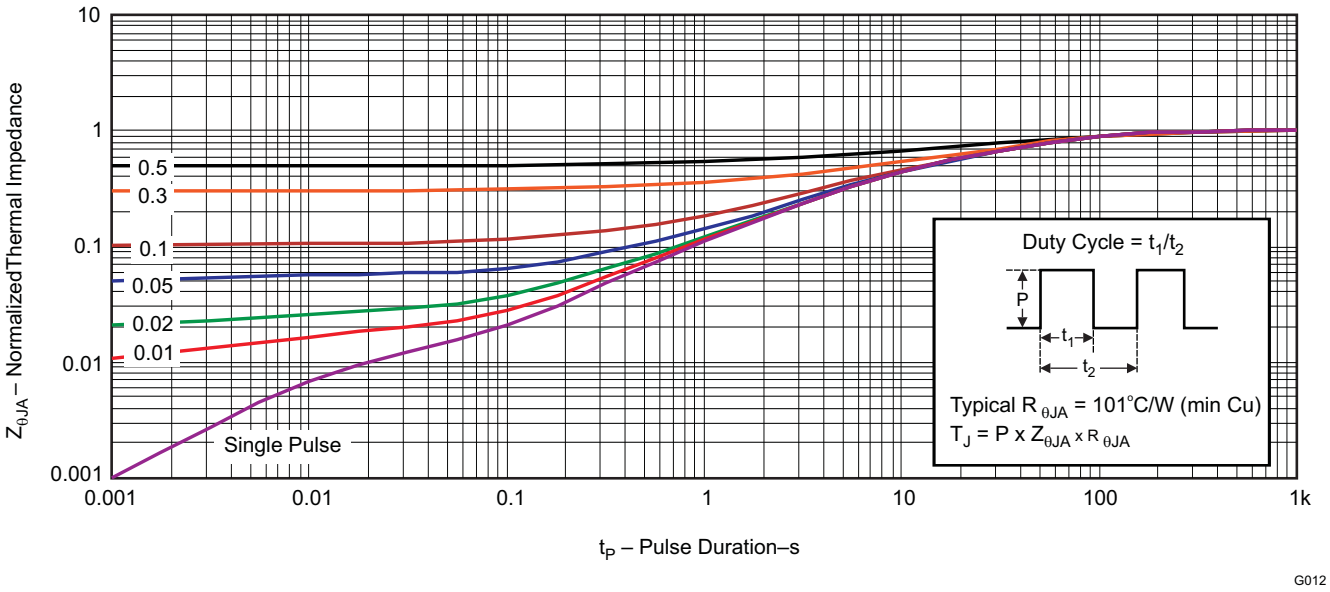


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

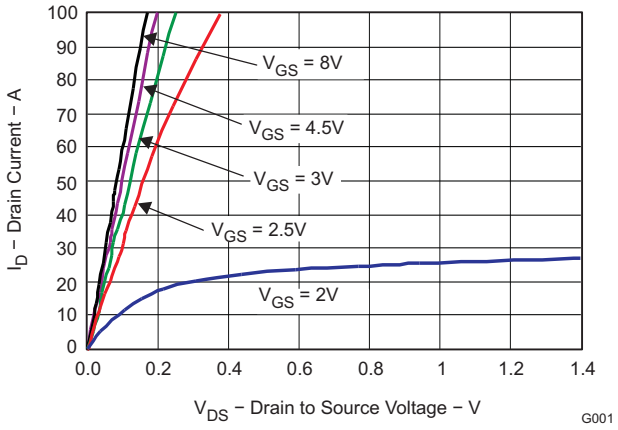


Figure 2. Saturation Characteristics

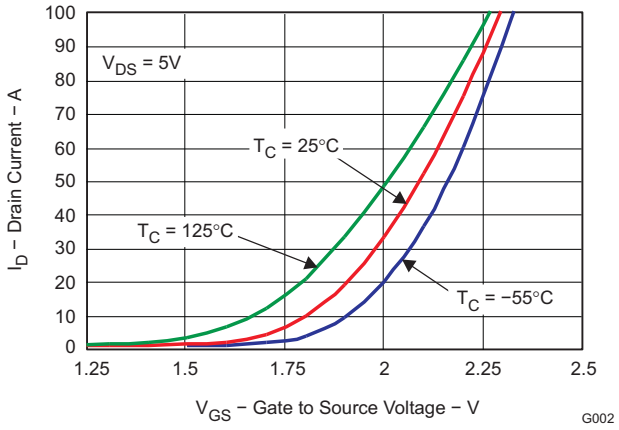


Figure 3. Transfer Characteristics

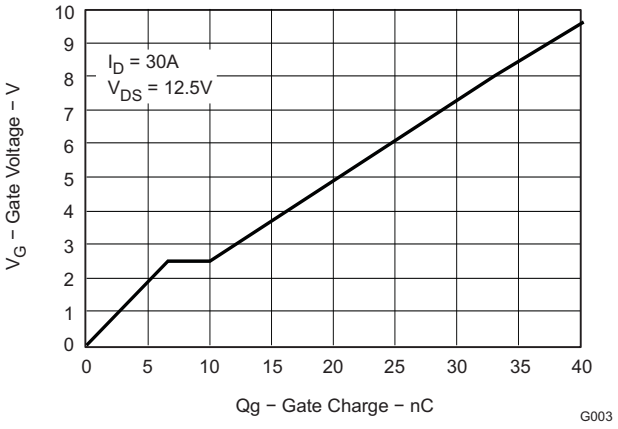


Figure 4. Gate Charge

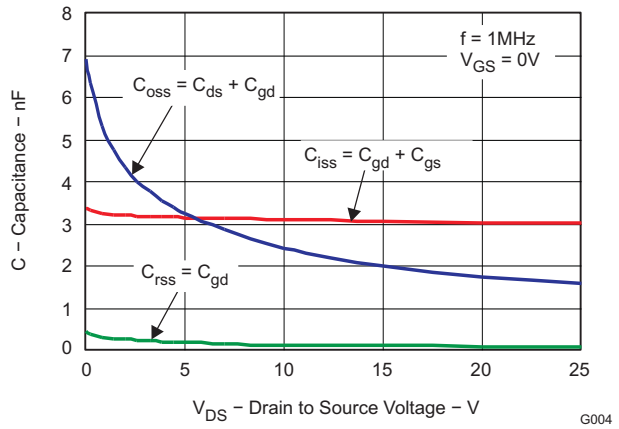


Figure 5. Capacitance

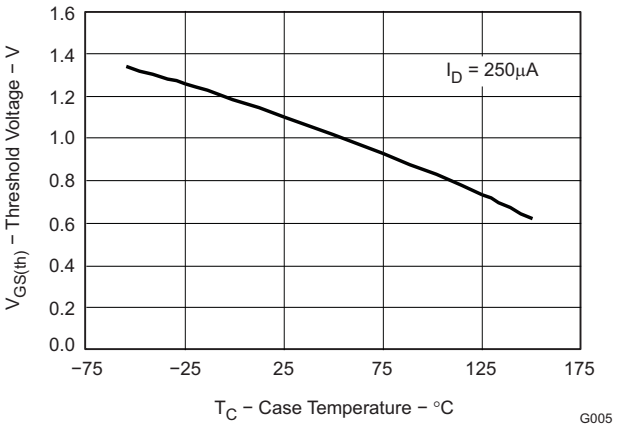


Figure 6. Threshold Voltage vs. Temperature

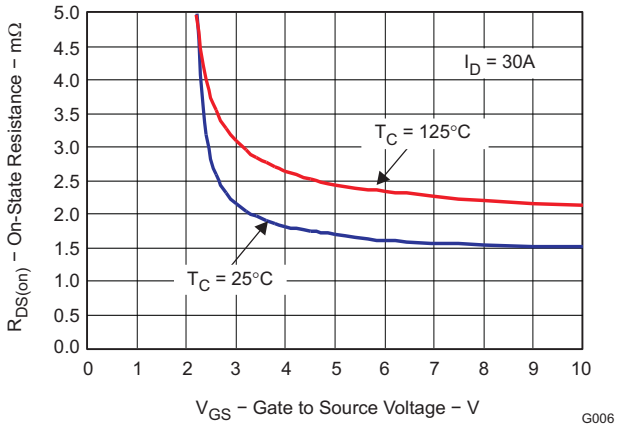


Figure 7. On Resistance vs. Gate Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

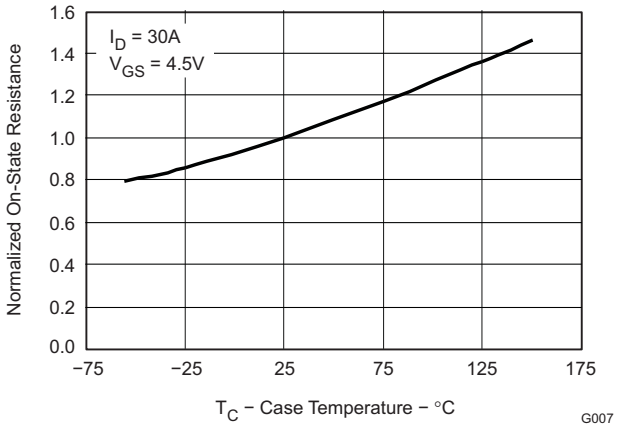


Figure 8. On Resistance vs. Temperature

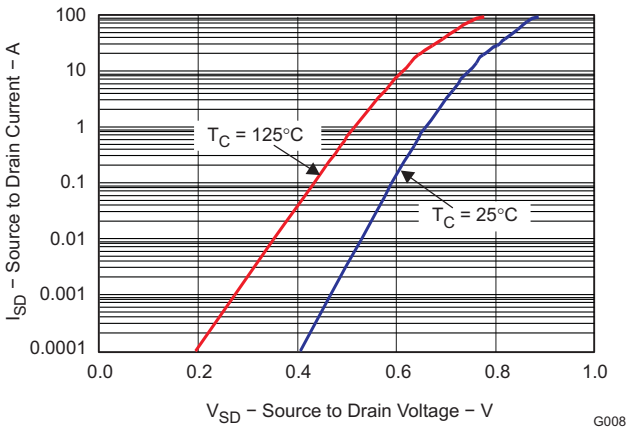


Figure 9. Typical Diode Forward Voltage

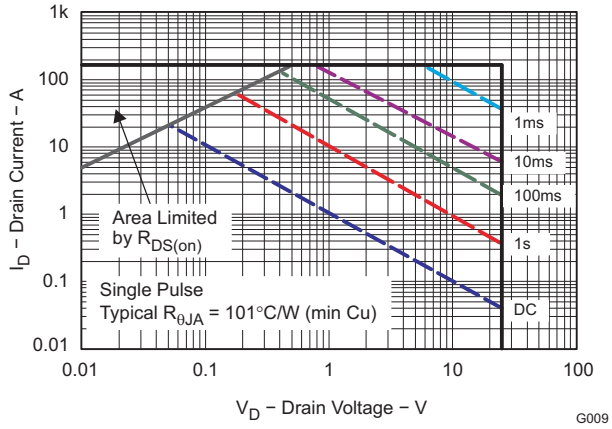


Figure 10. Maximum Safe Operating Area

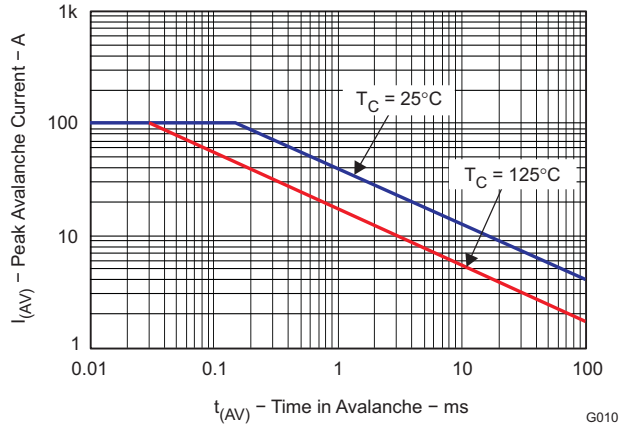


Figure 11. Single Pulse Unclamped Inductive Switching

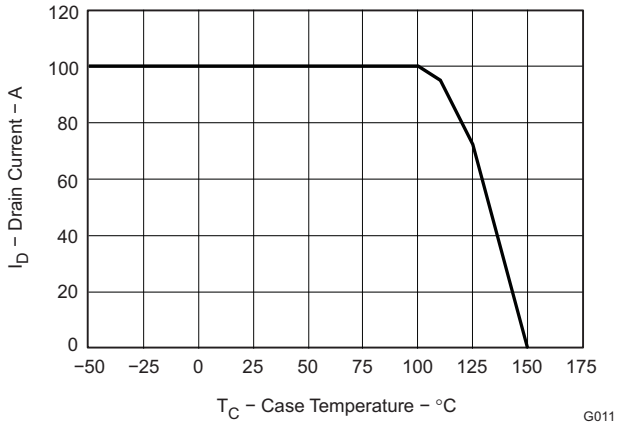
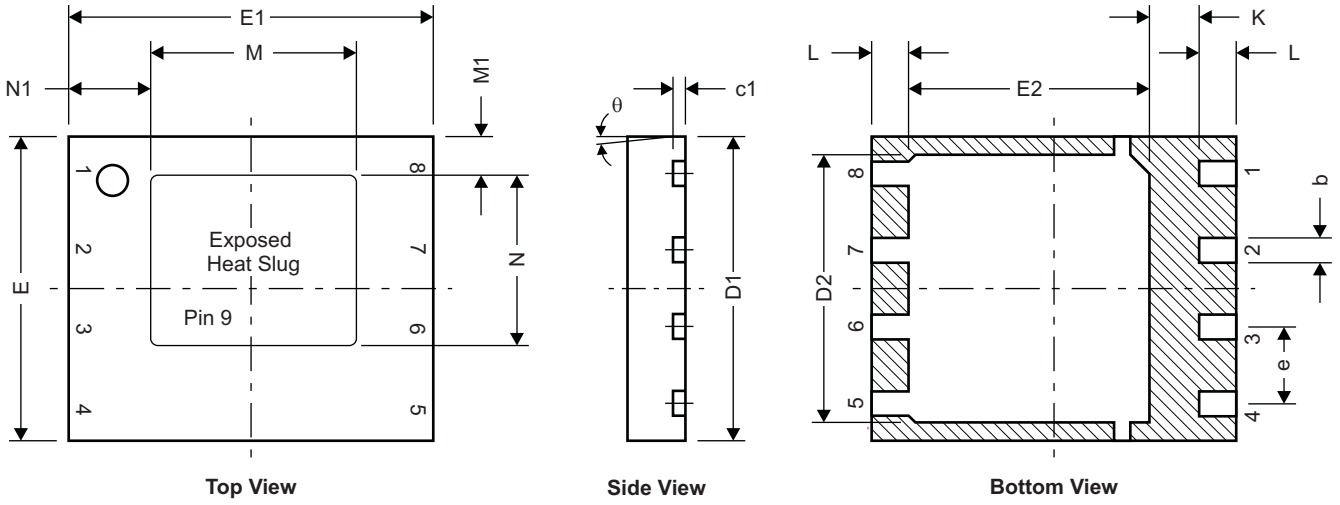
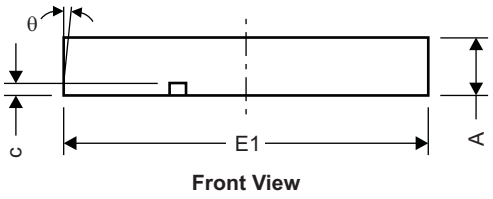


Figure 12. Maximum Drain Current vs. Temperature

MECHANICAL DATA

Q5C Package Dimensions



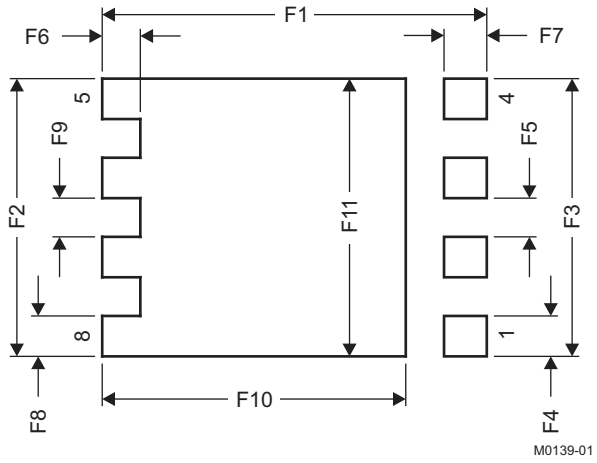


DualCool™ Pinout	
Pin#	**Label**
1, 2, 3, 9	**Source**
4	**Gate**
5, 6, 7, 8	**Drain**

M0162-01

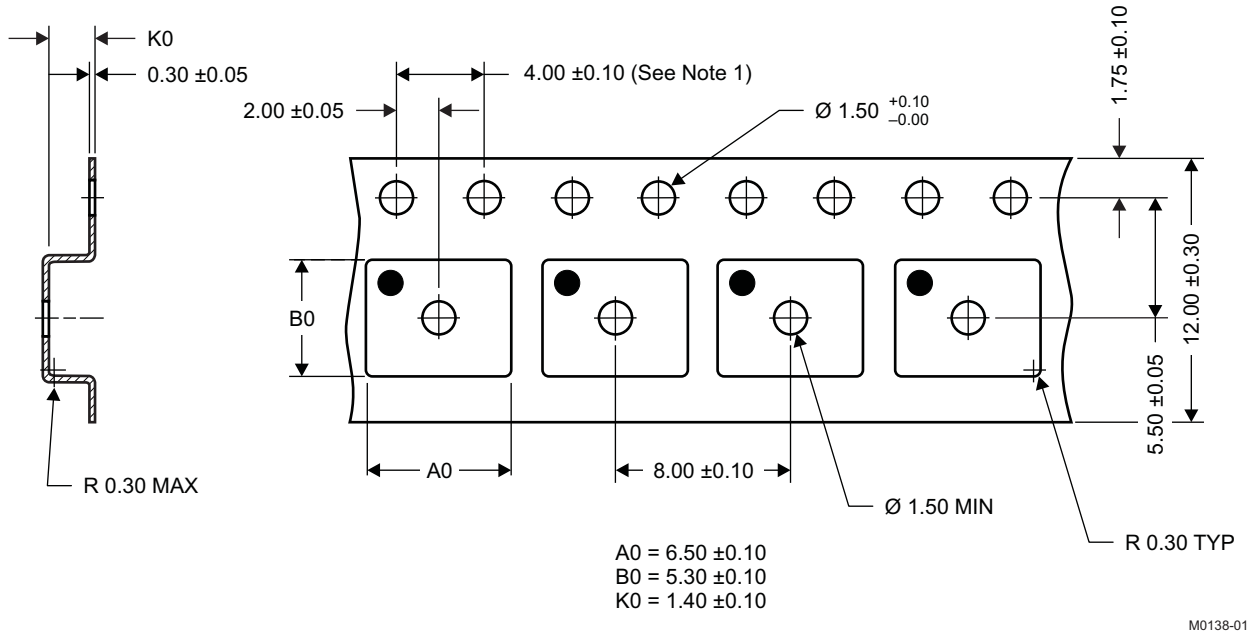
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
L	0.510	0.710	0.020	0.028
θ	–	–	–	–
K	0.760	–	0.030	–
M	3.260	3.460	0.128	0.136
M1	0.520	0.720	0.020	0.028
N	2.720	2.920	0.107	0.115
N1	1.227	1.427	0.048	0.056

Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

Q5C Tape and Reel Information



Notes:

1. 10-sprocket hole-pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm, unless otherwise specified.
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
6. MSL1 260°C (IR and convection) PbF reflow compatible

REVISION HISTORY

Changes from Original (December 2009) to Revision A **Page**

- Changed the labels on the Bottom View pinout image 1
- Changed the Mechanical Data dimensions table. Added dimensions for M, M1, N and N1 6

Changes from Revision A (April 2010) to Revision B **Page**

- Changed $R_{DS(on)}$ - V_{GS} = 3V in the Electrical Characteristics table From: 2.7 To: 2.9 in the max column 2
- Deleted the Package Marking Information section 7

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